

Docket No.: 300.1152

Serial No. 10/821,915

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please CANCEL claim 2 and AMEND claims 1, 3, 4, 5 and 6 in accordance with the following:

1. (CURRENTLY AMENDED) A semiconductor package obtained by collectively fabricating a plurality of semiconductor packages on a wafer in a batch process producing a wafer product and dicing the ~~resulting~~ wafer product into discrete semiconductor packages, wherein:

said semiconductor package is a stacked body formed by bonding two or more semiconductor devices through an insulating layer;

each of said semiconductor devices comprises a substrate and a device pattern formed on a surface thereof; and

a device pattern surface of a lower semiconductor device faces a non-device pattern surface of a semiconductor device stacked on said lower semiconductor device, and wherein said semiconductor device positioned, in sequence, as lowermost layers further comprises a back surface protective film and a heat radiation layer, of a material having a high heat transfer rate, on the non-device pattern surface of the wafer.

2. (CANCELLED)

3. (CURRENTLY AMENDED) A The semiconductor package as defined in claim 21, wherein said heat radiation layer is ~~one~~-deposited on the non-device pattern surface of a wafer as the lowermost layer, before said semiconductor packages are diced.

4. (CURRENTLY AMENDED) A The semiconductor package as defined in claim 21, wherein said heat radiation layer is one formed by a thin film formation technology.

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5. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 21, wherein said heat radiation layer is made of copper, aluminum or an alloy.

6. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 21, wherein said heat radiation layer also acts as a support.

7. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 1, wherein said insulating layer comprises a polyimide resin or an epoxy resin.

8. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 1, wherein said semiconductor device positioned as the uppermost layer further comprises a resin sealing layer on the device pattern surface thereof, and said resin sealing layer is one formed on the device pattern surface of the wafer as the uppermost layer, before said semiconductor package is diced.

9. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 1, wherein the device patterns of said semiconductor devices stacked are electrically connected to one another through a re-wiring layer and a substrate through-electrode that are simultaneously formed in one semiconductor device.

10. (CURRENTLY AMENDED) A-The semiconductor package as defined in claim 9, wherein each of said re-wiring layer and said substrate through-electrode is formed of copper or its alloy.

11. (CANCELLED)

12. (CANCELLED)

13. (CANCELLED)

14. (CANCELLED)

15. (CANCELLED)

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16. (CANCELLED)

17. (CANCELLED)

18. (CANCELLED)